TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

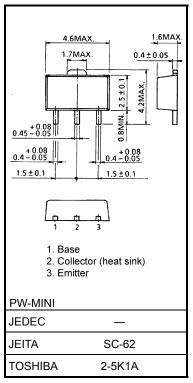
2SA1201

Voltage Amplifier Applications Power Amplifier Applications

- High voltage: VCEO = -120 V
- High transition frequency: $f_T = 120 \text{ MHz}$ (typ.)
- Small flat package
- $P_C = 1$ to 2 W (mounted on a ceramic substrate)
- Complementary to 2SC2881

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	-120	V	
Collector-emitter voltage	V _{CEO}	-120	V	
Emitter-base voltage	V _{EBO}	-5	V	
Collector current	Ι _C	-800	mA	
Base current	Ι _Β	-160	mA	
Collector power dissipation	P _C	500	mW	
	P _C (Note 1)	1000		
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	



Weight: 0.05 g (typ.)

Note 1: Mounted on a ceramic substrate (250 mm² × 0.8 t)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

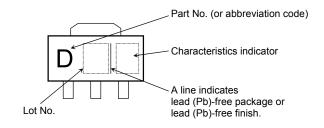
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Electrical Characteristics (Ta = 25°C)

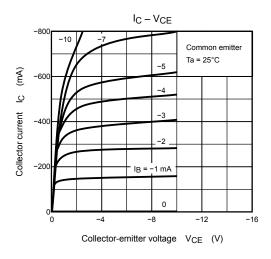
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -120 \text{ V}, \text{ I}_{E} = 0$	_	_	-0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 V, I_C = 0$	_	_	-0.1	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = -10 mA, I _B = 0	-120	—	—	V
Emitter-base breakdown voltage	V (BR) EBO	$I_{\rm E} = -1 {\rm mA}, I_{\rm C} = 0$	-5	_	_	V
DC current gain	h _{FE} (Note 3)	V _{CE} = -5 V, I _C = -100 mA	80	_	240	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = -500 mA, I _B = -50 mA	_	—	-1.0	V
Base-emitter voltage	V _{BE}	V _{CE} = -5 V, I _C = -500 mA	_	_	-1.0	V
Transition frequency	f _T	V _{CE} = -5 V, I _C = -100 mA	—	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = −10 V, I _E = 0, f = 1 MHz	_	—	30	pF

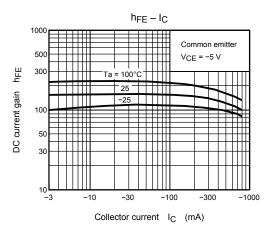
Note 3: h_{FE} classification O: 80 to 160, Y: 120 to 240

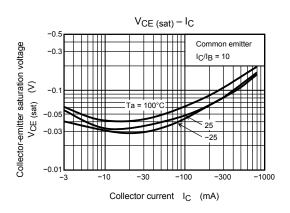
Marking

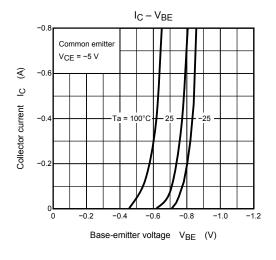


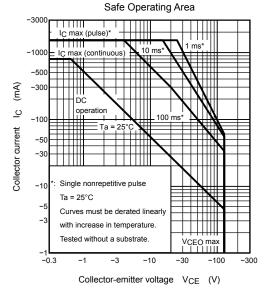
TOSHIBA

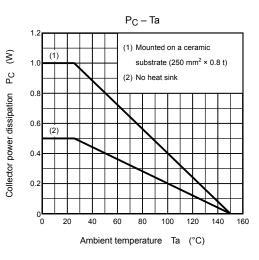












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